

Sheet 1 of 1

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 119498		APPLICATION NO. 10/826,354	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT Hiromi OTOMA		EXAMINER: CHUC TRAN	
				FILING DATE April 19, 2004		GROUP 2828 2821	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
TC	1.	JP A 2002-185079 w/abstract & transl.	6/28/2002	JAPAN			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
TC	2.	Kenichi IGA; "Surface Emitting Laser"; IEICE Transactions C-1, Vol. J81-C-1, No. 9; September 1998; pp 483-493					
	3.	H. OTOMA et al.; "Fabrication and Performance of 12 X 12 Matrix-Addressed 780nm Oxide-Confined Vsel Array"; Bulletin of Solid State Physics and Applications; Vol. 5, No. 1.; 1999; pp 11-15					
TC	4.	Nobuaki UEKI et al.; "Single-Transverse-Mode 3.4-mW Emission of Oxide-confined 780-nm Vsel's"; IEEE Photonics Technology Letters; Vol. 11, No. 12; December 1999; pp 1539-1541					
	5.	Jun SAKURAI et al.; "10 Gb/s Surface Emission Semiconductor Laser"; Electronic Materials, Vol. 41, No. 11; November 2002; pp 49-52					
TC	6.	M. Grabherr et al.; "Efficient Single-Mode Oxide-Confined GaAs VCSEL's Emitting in the 850-nm Wavelength Regime"; IEEE Photonics Technology Letters; Vol. 9, No. 10.; October 1997; pp 1304-1306					
	7.	Aaron et al.; "Aperture Placement Effects in Oxide-Defined Vertical-Cavity Surface-Emitting Lasers"; IEEE Photonics Technology Letters; Vol. 10, No. 10; October 1998; pp 1362-1364					
EXAMINER				DATE CONSIDERED			
				10/13/05			
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: July 29, 2004